



Title of Change:	Hydrazine elimination of ON Semiconductor Niigata Co., Ltd. (OSNC).													
Proposed First Ship date:	17 January 2019													
Contact Information:	Contact your local ON Semiconductor Sales Office or < Tetsuya.Fukushima@onsemi.com >													
Samples:	Contact your local ON Semiconductor Sales Office or < PCN.Samples@onsemi.com > Sample requests are to be submitted no later than 30 days from the date of first notification, Initial PCN or Final PCN, for this change.													
Type of Notification:	This is an Initial Product/Process Change Notification (IPCN) sent to customers. IPCNs are typically issued 30 days prior to the issuance of the Final Change Notice (FPCN). An IPCN is an advance notification about an upcoming change and contains general information regarding the change details and devices affected. It also contains the preliminary reliability qualification plan. The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN). This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 90 days prior to implementation of the change. In case of questions, contact <PCN.Support@onsemi.com>													
Change Part Identification:	Date Code													
Change Category:	☒ Wafer Fab Change ☐ Assembly Change ☐ Test Change ☐ Other _____													
Change Sub-Category(s):	☐ Manufacturing Site Addition ☐ Material Change ☐ Datasheet/Product Doc change ☐ Manufacturing Site Transfer ☐ Product specific change ☐ Shipping/Packaging/Marking ☒ Manufacturing Process Change ☐ Other: _____													
Sites Affected:	ON Semiconductor Sites: ON Niigata, Japan	External Foundry/Subcon Sites: None												
Description and Purpose: This Initial notification announces the elimination of Hydrazine in ON Semiconductor Niigata Co., Ltd. (OSNC) Japan for parts listed in this PCN. The related products are transferred to a process that does not use Hydrazine on the same site ON Semiconductor Niigata Co., Ltd. (OSNC) Japan. <table border="1" style="width: 100%; text-align: center;"> <thead> <tr style="background-color: #92d050;"> <th>Change Point</th> <th>Before Change Description</th> <th>After Change Description</th> </tr> </thead> <tbody> <tr> <td>Fab (OSNC)</td> <td>N1 Fab (Minimum rule=0.8um, Class=100)</td> <td>N1 Fab (Minimum rule=0.8um, Class=100) AND N2 Fab (Minimum rule=0.25um, Class=10)</td> </tr> <tr> <td>Wire material</td> <td>Aluminum (without Anti-reflected Layer)</td> <td>Aluminium (with Anti-reflected Layer)</td> </tr> <tr> <td>Interlayer material</td> <td>Silicon nitride and Polyimide or Polyimide</td> <td>Silicon nitride and Silicon oxide or Oxide</td> </tr> </tbody> </table>			Change Point	Before Change Description	After Change Description	Fab (OSNC)	N1 Fab (Minimum rule=0.8um, Class=100)	N1 Fab (Minimum rule=0.8um, Class=100) AND N2 Fab (Minimum rule=0.25um, Class=10)	Wire material	Aluminum (without Anti-reflected Layer)	Aluminium (with Anti-reflected Layer)	Interlayer material	Silicon nitride and Polyimide or Polyimide	Silicon nitride and Silicon oxide or Oxide
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**Qualification Plan:**QV DEVICE NAME: LB11870-TRM-EPACKAGE: HSSOP48 (375 mil)

Test	Specification	Condition	Interval
HTOL	JESD22-A108	Tj=150°C, 100 % max rated Vcc	1008 hrs
HTSL	JESD22-A103	Ta= 150°C	1008 hrs
TC	JESD22-A104	Ta= -65°C to +150°C	500 cyc
THB	JESD22-A101	85°C, 85% RH, bias	1008 hrs
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig,	96 hrs
PC	J-STD-020 JESD-A113	MSL 3 @ 260 °C	-
HBM	JS001	100pF,1.5kohm	-
CDM	JS002		-

QV DEVICE NAME: LA4440J-K-EPACKAGE: SIP14H

Test	Specification	Condition	Interval
HTOL	JESD22-A108	Tj=150°C, 100 % max rated Vcc	1008 hrs
HTSL	JESD22-A103	Ta= 150°C	1008 hrs
TC	JESD22-A104	Ta= -65°C to +150°C	500 cyc
HAST	JESD22-A101	130°C, 85% RH, 18.8psig, bias	96 hrs
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig,	96 hrs
HBM	JS001	100pF,1.5kohm	-
CDM	JS002		-

List of Affected Parts:

Part Number	Qualification Vehicle
LA5759-MDB-E	LB11870-TRM-E
LB11620GP-TE-L-H	LB11870-TRM-E
LA6583MC-AH	LB11870-TRM-E
LA6584M-TLM-E	LB11870-TRM-E
LA6585MC-AH	LB11870-TRM-E
LA6585FA-BH	LB11870-TRM-E
LA6588MC-AH	LB11870-TRM-E
LB11620T-TLM-E	LB11870-TRM-E
LB11660FV-TLM-E	LB11870-TRM-E
LB11660FV-TLM-H	LB11870-TRM-E
LB11660RV-TLM-E	LB11870-TRM-E



LB11660RV-TLM-H	LB11870-TRM-E
LB11685AV-TLM-H	LB11870-TRM-E
LB11696V-TLM-E	LB11870-TRM-E
LB11850VA-TLM-E	LB11870-TRM-E
LB11850VA-TLM-H	LB11870-TRM-E
LB11867FV-TLM-E	LB11870-TRM-E
LB11867FV-TLM-H	LB11870-TRM-E
LB11867RV-TLM-E	LB11870-TRM-E
LB11867RV-TLM-H	LB11870-TRM-E
LB11868V-TLM-H	LB11870-TRM-E
LB11923V-TLM-E	LB11870-TRM-E
LB11961-TLM-E	LB11870-TRM-E
LB11961-TLM-H	LB11870-TRM-E
LB11961V-TLM-E	LB11870-TRM-E
LB11967V-TLM-E	LB11870-TRM-E
LB11967V-TLM-H	LB11870-TRM-E
LB11970FV-TLM-H	LB11870-TRM-E
LB1668M-TLM-E	LA4440J-K-E
LB1668M-TLM-H	LA4440J-K-E
LB1863M-TLM-E	LA4440J-K-E
LB1863M-TLM-H	LA4440J-K-E
LB1868M-TLM-E	LA4440J-K-E
LB1868M-TLM-H	LA4440J-K-E
LB1836ML-TLM-E	LB11870-TRM-E
LB1838M-TLM-E	LB11870-TRM-E
LB1848MC-BH	LB11870-TRM-E
LB8503V-TLM-E	LB11870-TRM-E

"Please be informed that there may be Customer Specific parts impacted by this Notification, thus MPN & CPN info will not be reflected in the parts list of this Generic document. Instead please click the link to the addendum PCN copy provided in the email notification to see full list of affected products specific to your company."